

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A plasma processing device, comprising:

a chamber ~~capable of maintaining~~ provided to maintain an atmosphere depressurized to less than atmospheric pressure;

a transfer pipe connected to the chamber;

a gas introduction mechanism ~~for introducing~~ provided to introduce a gas into the transfer pipe; [[and]]

a microwave supply source ~~for introducing~~ provided to introduce a microwave from outside to inside of the transfer pipe[[,]]; and

a light shield configured to block light emitted from the plasma and to allow passage of active species emitted from the plasma, the light shield being provided substantially in contact with an inner wall of the chamber at a part where the active species are introduced into the chamber, wherein

the plasma processing device ~~being capable of forming~~ is provided to form a plasma of the gas in the transfer pipe and ~~performing~~ to perform ashing processing ~~for removing to remove~~ a resist of a workpiece having a low-k material on which the resist is formed placed in the chamber, ~~wherein~~

the transfer pipe is connected to ~~have~~ an opening in [[an]] the inner wall of the chamber, the inner wall being generally perpendicular to a major surface of the workpiece, and

the workpiece is not provided [[on]] in a direct line of sight from the plasma.

Claim 2 (Currently Amended): A plasma processing device according to claim 1, wherein the transfer pipe is connected to the inner wall of the chamber with a tilt such that

[[its]] an axis line of the transfer pipe is directed away from the workpiece as compared to when the transfer pipe is connected generally perpendicular to the inner wall of the chamber.

Claim 3 (Currently Amended): A plasma processing device, comprising:

a chamber ~~capable of maintaining~~ provided to maintain an atmosphere depressurized to less than atmospheric pressure;

a transfer pipe connected to the chamber via a generally L-shaped connection pipe;

a gas introduction mechanism ~~for introducing~~ provided to introduce a gas into the transfer pipe; [[and]]

a microwave supply source ~~for introducing~~ provided to introduce a microwave from outside to inside of the transfer pipe[.,]; and

a light shield configured to block light emitted from the plasma and to allow passage of active species emitted from the plasma, the light shield being provided substantially in contact with an inner wall of the chamber at a part where the active species are introduced into the chamber, wherein

the plasma processing device ~~being capable of forming~~ is provided to form a plasma of the gas in the transfer pipe and ~~performing to perform~~ ashing processing for removing to remove a resist of a workpiece having a low-k material on which the resist is formed placed in the chamber, wherein

the connection pipe is connected to ~~have~~ an opening in [[an]] the inner wall of the chamber, the inner wall being generally opposed to a major surface of the workpiece, and

the connection pipe has an inner wall made of a fluorine-containing resin.

Claim 4 (Canceled).

Claim 5 (Currently Amended): A plasma processing device, comprising:

a chamber ~~capable of maintaining~~ provided to maintain an atmosphere depressurized to less than atmospheric pressure;

a transmission window ~~occupying~~ provided to occupy part of a wall of the chamber;

a microwave supply source ~~for introducing~~ provided to introduce a microwave from outside to inside of the chamber via the transmission window; and

a gas introduction mechanism ~~for introducing~~ provided to introduce a gas into the chamber, wherein

the plasma processing device ~~being capable of forming~~ provided to form a plasma of the gas in the chamber and ~~performing~~ to perform plasma processing on a workpiece placed in the chamber, ~~wherein~~ and

a light shield ~~for blocking~~ configured to block light emitted from the plasma and ~~for allowing~~ to allow passage of active species emitted from the plasma is provided ~~near~~ substantially in contact with an inner wall of the chamber at a part where the active species are introduced into the chamber.

Claim 6 (Currently Amended): A plasma processing device according to ~~any one of~~ claims 1, ~~[[to]]~~ 2, 3, or 5, further comprising rectifying means for regulating distribution of gas flow on the workpiece, the gas flow being supplied from the transfer pipe.

Claim 7 (Currently Amended): A plasma processing device according to ~~any one of~~ claims 1, ~~to 6~~ 2, 3, or 5, wherein an absorber ~~for absorbing~~ to absorb light emitted from the plasma is provided on at least one of the inner wall of the chamber and an inner wall of the transfer pipe.

Claim 8 (Currently Amended): An ashing method for removing a resist of a workpiece having an insulating layer on which the resist is formed, comprising:

forming a plasma containing hydrogen and an inert gas;

allowing active species emitted from the plasma to act on the workpiece placed in a chamber ~~capable of maintaining~~ that is provided to maintain an atmosphere depressurized to less than atmospheric pressure; and

removing the resist in a condition that light emitted from the plasma is blocked by a light shield which is substantially in contact with an inner wall of the chamber at a part where the active species are introduced into the chamber.

Claim 9 (Original): An ashing method according to claim 8, wherein the inert gas is helium.

Claim 10 (Original): An ashing method according to claim 8 or 9, wherein the insulating layer comprises a low-k material.